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1. MOSFET
- Accumulation, Depletion, Threshold, Inversion
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1. MOSFET -
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Semiconductor Physics and Devices, Donald Neamen, Fourth Edition, 2012, McGraw-Hill

Ben G. Streetmann, Solid State Electronic Devices, Prentice-Hall
Anderson, Fundamentals of Semiconductor Devices, McGraw-Hill

Chapter Checkpoint, Review Questions, Problems Chapter
1 .

- 1 : Metal-Semiconductor Junction
- 2 : MOS Structure
- 3 : C-V Characteristics of MOS
- 4 : MOSFET Operation
- 5 : Nonideal Effects
- 6 : Scaling
- 7 : Threshold Voltage and Secondary Effects
- 8 :
- 9 : Bipolar Transistor Action and Carrier Distribution
- 10 : Low Frequency Gain
- 11 : Nonideal Effects, Frequency Limitations and Large-Signal Switching
- 12 : Optical Absorption and Solar Cells
- 13 : Photodetection and PL &EL
- 14 : LED and LD
- 15 :

MOSFET ,
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